

**Oxford Instruments - Atomic Layer Deposition (ALD) System - OpAL  
THICKNESS CONTROL AT THE ATOMIC SCALE**



- Wafer: Up to 200mm wafers & pieces directly on stage
- Bubbled Liquid and Solid Precursors: Up to 3
- Max Precursor Source Temperature: 200°C (Jacket)
- Thermal Gas Precursors = 2 internally
- Plasma Gases = Up to 8 in externally mounted gas pod
- Wafer Stage Temperature Range: 25°C - 400°C
- Current precursor available: Al<sub>2</sub>O<sub>3</sub>